Autorney's Docket No. 5308-157IP2

PATENT

1762 14W

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

: Das et al.

rial No.: 10/045,542

Filed: October 26, 2001 For: METHOD OF FA Confirmation No.: 3570 Group Art Unit: 1762

Examiner: Michael. E. Barr

METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON CARBIDE

LAYER UTILIZING AN ANNEAL IN A HYDROGEN ENVIRONMENT

Date: September 21, 2004

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

In accordance with the requirements of 37 C.F.R. § 1.97(c)(2), a check for the \$180.00 fee specified in 37 C.F.R. § 1.17(p) is enclosed. This amount is believed to be correct; however, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

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Respectfully submitted,

Timothy J. O'Sullivan Registration No. 35,632

Customer Number: 20792

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

September 21, 2004

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		OTHER DOO	CUMENTS (In	ncluding Author	, Title, Date, Pe	ertinent Pages	, Etc.)	
	1	Wang et al. "The Effects of NH ₃ Plasma Passivation on Polysilicon Thin-Film Transistors," <i>IEEE Electron Device Letters</i> , Vol. 16, No. 11, November 1995, pp. 503-5.						
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